

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-16. (cancelled)

17. (currently amended) A product (10) ~~usable~~ configured as a starting substrate for ~~[[the]]~~ a manufacture of micro-electronic and/or micro-mechanic devices, comprising:

wafer (10) of a semi-conducting or conducting material, and having a first (14) and a second (16) surface, the wafer comprising one or more local depressions (75) in at least one surface thereof;

at least one electrically conducting member (12) extending through said wafer,

~~characterized in that~~ wherein

the electrically conducting member (12) is insulated from surrounding material of the wafer by a finite layer (15) of an insulating material; and ~~in that~~

~~it~~ the electronically conducting member (12) comprises ~~[[the]]~~ a same material as the wafer, i.e. it is made from the wafer material, and

the at least one electrically conductive member is essentially flush with a bottom surface of said one or more depressions.

18. (previously presented) The product as claimed in claim 17, wherein said wafer is a semiconductor wafer.

19. (previously presented) The product as claimed in claim 18, wherein said wafer is a silicon wafer.

20. (currently amended) The product as claimed in claim 17, wherein said wafer has a thickness of 200 - 5000 μm , ~~preferably 300 - 3000 μm , most preferably 400 - 1000 μm .~~

21. (currently amended) The product as claimed in claim 17, wherein ~~[[the]]~~ a thickness of the finite layers of insulating material is 1-20 μm , ~~typically 8-12 μm .~~

22. (currently amended) The product as claimed in claim 17, wherein ~~[[the]]~~ a pitch/center-to-center distance between the ~~electrical connections~~ electronically conducting members is larger than 10 μm , ~~typically 50-100 μm .~~

23. (previously presented) The product as claimed in claim 17, wherein the wafer is essentially flat.

24. (cancelled)

25. (currently amended) A Micro-Electrical-Mechanical System (MEMS) device, comprising:

solder bumps for flip-chip mounting placed on the a backside of the device, and having wafer through electrical interconnections (vias, 12), wherein the electrical interconnections (12) are insulated from surrounding material of the wafer by a finite layer (15) of an insulating material, wherein the a material of the interconnections comprise the a same material as the wafer, i.e. it is made from the wafer material.

26-27. (cancelled)

28. (new) The product as claimed in claim 17, wherein said wafer has a thickness of 300 - 3000 μm .

29. (new) The product as claimed in claim 17, wherein said wafer has a thickness of 400 - 1000 μm .

30. (new) The product as claimed in claim 17, wherein a thickness of the finite layers of insulating material is 8-12 μm .

31. (new) The product as claimed in claim 17, wherein a pitch/center-to-center distance between the electronically conducting members is 50-100 μm .

32. (new) The product as claimed in claim 17, wherein the insulating material is an oxide.

33. (new) The product as claimed in claim 17, wherein the insulating material is TEOS.

34. (new) The product as claimed in claim 17, wherein the wafer is provided with a cavity reaching down to exposed ends of the electrically conducting members.

35. (new) The product as claimed in claim 17, wherein the wafer is provided with a cavity reaching down to exposed ends of the electrically conducting members, and a deflectable membrane is provided over the cavity.

36. (new) The product as claimed in claim 35, wherein the membrane is configured to be actuated by a voltage applied to the electrically conducting members.

37. (new) The product as claimed in claim 17, wherein the wafer is provided with a cavity reaching down to exposed ends

of the electrically conducting members, and a deflectable array of micro mirrors is provided over the cavity.

38. (new) The product as claimed in claim 37, wherein the array of micro mirrors are configured to be actuated by a voltage applied to the electrically conducting members.

39. (new) The device as claimed in claim 25, wherein the wafer has one or more local depressions in at least one surface thereof, and the electrical interconnections are essentially flush with a bottom surface of said one or more depressions.